



**Faculty of Engineering & Technology Electrical & Computer
Engineering Department**

Interfacing Techniques – ENCS4380

HW #2

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Section: 1

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Question 1

```
1 % Maha Mali 1200746
2 % System Parameters
3 m = 1; % Mass of the sensor
4 b = 0.2; % Damping coefficient
5 % Transfer Function
6 numerator = 1;
7 denominator = [m, b, 0];
8 sys = tf(numerator, denominator);
9 % Step Response
10 figure;
11 step(sys, 'r'); % Adds 'r' to specify red color
12 title('Step Response of Acceleration Sensor Model');
13
14 % Ramp Response
15 figure;
16 impulse(sys, 'r'); % Adds 'r' to specify red color
17 title('Impulse Response of Acceleration Sensor Model');
18 % Frequency Response
19 figure;
20 bode(sys, 'r'); % Adds 'r' to specify red color
21 title('Frequency Response of Acceleration Sensor Model');
```

Figure 1: Question 1 MATLAB Code

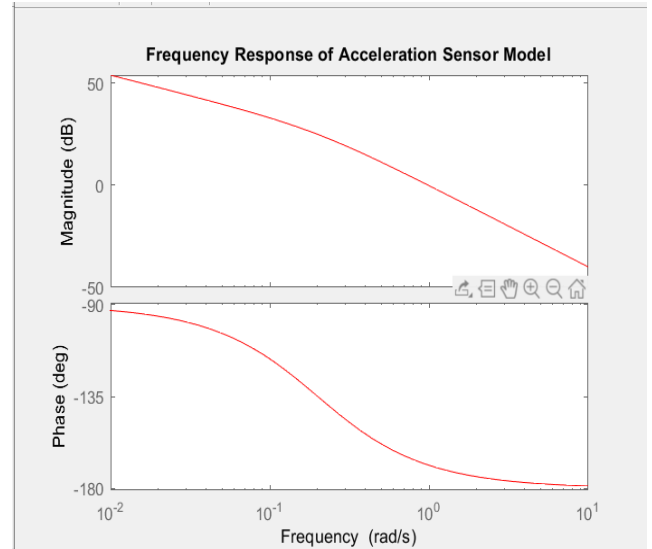


Figure 2: Frequency Response

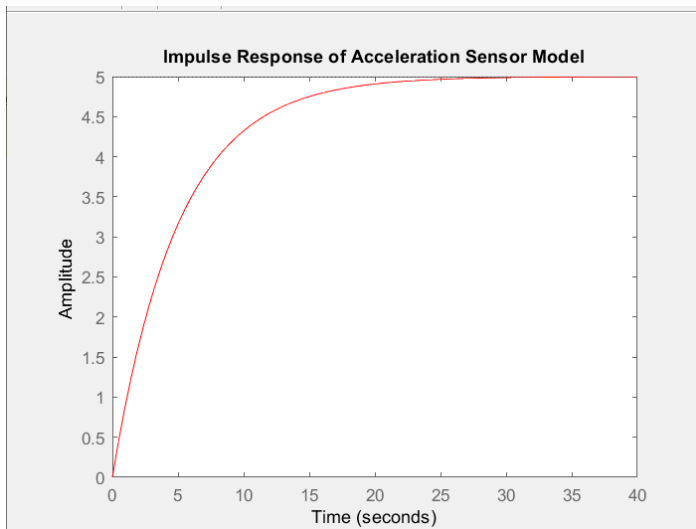


Figure 3: Impulse Response

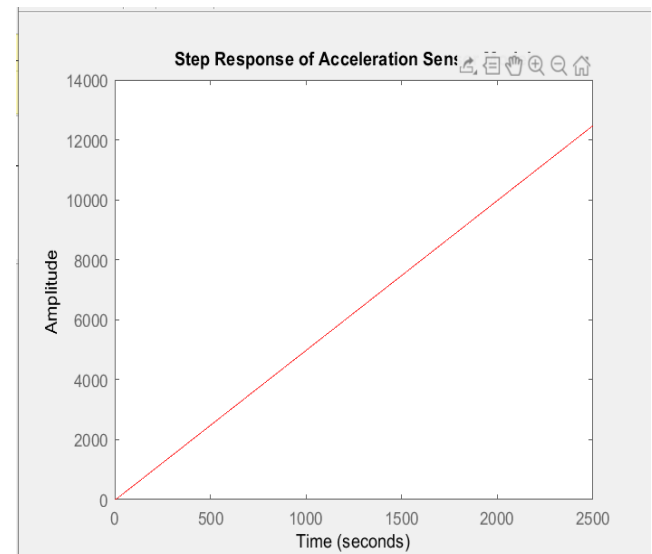


Figure 4: Step Response

❖ The Effect Of B/M On the System Response:

Unit step Response: if we increase the B/M accelerates damping yielding fast response, also high B/M may cause overshooting and oscillations. On the other hand, decreasing B/M slows damping resulting in a more gradual response, this can reduce overshoot, but response may be slower.

Ramp Response: if we increase the B/M values this will lead to faster response to ramps. On the other hand, lower B/M values this will result in a slower response with clear oscillations.

❖ The Effect Of B/M On the Frequency Response:

Bandwidth: if we increase the B/M values the system can respond to a wider range of frequencies. On the other hand, decreasing B/M values leads to a narrower bandwidth and the system has a more specific frequencies value.

Response Frequency: if we increase the B/M values the system is more affected to resonance at lower frequencies. On the other hand, lower B/M values the system is less open to resonance at higher frequencies.

Question 2

❖ Accelerometer

- **Concept of Operation:** the accelerometer in smartphone measures the linear acceleration of the device. When at rest position in whatever orientation.
- **Technology Used in Manufacturing: MEMS** (Micro – Electro -Mechanical Systems).
- **Static and dynamic characteristics:** the static characteristics: sensitivity which is ratio of the output signal to applied acceleration, resolution which is the smallest detectable change in acceleration. The dynamic characteristics: bandwidth which is range of frequencies for accurate measurements, frequency response which is describe how well the accelerometer responds to change in acceleration over time.
- **Simple interface:** using APIs.

❖ Gyroscope

- **Concept of Operation:** The gyroscope sensor is responsible for the autorotation of the screen and view on the screen whenever a phone is rotated.
- **Technology Used in Manufacturing: MEMS** (Micro – Electro -Mechanical Systems).
- **Static and dynamic characteristics:** the static characteristics: sensitivity and zero rate output which is the gyroscope output when there is no rotation. The dynamic characteristics: dynamic range the range of angular velocities that the gyroscope can accurately measure.

- ❖ **Finger print:** it can read and store biometric data of our fingers and can be used to unlock the phone. Also, it can use the capacitance of the finger to detect that the thing which touches the button is a humanly thing.

Question 3

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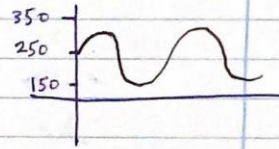
Q3 Given: time constant (τ) = 1.2s
 temperature change between 150 & 350C
 periodic (T) = 10s

DC = $\frac{350+150}{2} = \boxed{250}$

P-P Value = $350-150 = \boxed{200} \Rightarrow A$ (Amplitude)

$$X(t) = DC + \frac{P-P}{2} \sin\left(\frac{2\pi t}{T}\right)$$

$$= 250 + \frac{200}{2} \sin\left(\frac{2\pi t}{10}\right)$$



$$y(t) = \frac{A}{\sqrt{1+(\omega\tau)^2}} \sin(\omega t - \tan^{-1}(\omega\tau)) + DC$$

$$\omega = 2\pi f = \frac{2\pi}{T} = \frac{2\pi}{10} = \boxed{\frac{\pi}{5}}$$

$$= \frac{100}{\sqrt{1+(\frac{\pi}{5} \cdot 1.2)^2}} \cdot \sin\left(\frac{\pi}{5}t - \tan^{-1}\left(\frac{1.2\pi}{5}\right)\right) + 250$$

2.3 Time shift

$$= 2.3 \cdot \sin\left(\frac{\pi}{5}t - \tan^{-1}\left(\frac{1.2\pi}{5}\right)\right) + 250$$

$$= 2.3 \cdot \sin\left(\frac{\pi}{5}t - 37\right) + 250$$

\Rightarrow Maximum Value = $250 + 2.3 = \boxed{252.3}$ *
 , When $\sin(\theta) = 1$

\Rightarrow Minum Value = $250 - 2.3 = \boxed{247.7}$ *
 When $\sin(\theta) = -1$

phase shift = $\frac{\text{Time lag} \cdot 360}{\text{Period}}$

$37 = \frac{\text{Time lag} \cdot 360}{\text{Period } 10}$

$\boxed{\text{Time lag} = 1.027 \text{ sec}}$ *

Figure 5: Question 3 Solution

Question 4

Q4/

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1) Calculate the signal voltage at output ($V_{s,out}$)

⇒ From question given the signal voltage at input
($V_{s,in}$) = 6 MV

⇒ gain of amplifier (G) = 80

$$V_{s,out} = V_{s,in} * G = 6 \text{ MV} * 80 = ~~480 \text{ MV}~~ \quad \boxed{480 \text{ MV}}^*$$

2) Calculate the total noise voltage at output ($V_{n,out}$)

⇒ From question given the noise voltage at input
($V_{n,in}$) = 1 MV

⇒ noise added by Amplifier ($V_{n,Amp}$) = $\boxed{2 \text{ MV}}$

$$V_{n,out} = V_{n,in} + V_{n,Amp} = 1 \text{ MV} + ~~2 \text{ MV}~~ = \boxed{3 \text{ MV}}$$

3) Calculate the signal Noise Ratio (~~At~~ SNR) at output

$$SNR = \frac{V_{s,out}}{V_{n,out}} = \frac{~~480 \text{ MV}~~}{~~3 \text{ MV}~~}$$

$$SNR = \frac{\boxed{480 \text{ MV}}}{\boxed{3 \text{ MV}}} = \boxed{160 \text{ MV}}^*$$

$$\boxed{SNR = 160 \text{ MV}}$$

Figure 6: Question 4 Solution

Question 5

The below equation given from question, also given $V_s = 3.3\text{ V}$ and $P_{in} = 100\text{ kPa}$

$$V_{out} = V_s * (0.004 * P_{in} - 0.04)$$

Nominal sensitivity: This is the change in output voltage per unit change in pressure at the nominal supply voltage.

Nominal offset: This is the output voltage at zero pressure.

Q5) Maha Mali 1200246

1) if $V_s = 3.3\text{ V}$

⇒ for nominal Sensitivity $V_s = 1$

$$V_{out} = V_s (0.004 P_{in} - 0.04) = 1 * (0.004 * 100 - 0.04) = 0.36\text{ V}$$

⇒ for nominal offset: $V_s = 3.3\text{ V}$

$$V_{out} = V_s (0.004 P_{in} - 0.04) = 3.3 * 0.36 = 1.188\text{ V}$$

2) Give Sensor fluctuates from 2.85 V DC to 3.5 V DC

⇒ $V_{s(max)} = 3.5\text{ V}$

$$V_{out(max)} = V_{s(max)} (0.004 P_{in} - 0.04) = 3.5 (0.004 * 100 - 0.04) = 3.5 * 0.36 = 1.26\text{ V}$$

Maximum absolute error = $|V_{out(nominal\ offset)} - V_{out(max)}|$

$$= |1.188 - 1.26| = 0.072$$

⇒ $V_{s(min)} = 2.85\text{ V}$

$$V_{out(min)} = V_{s(min)} (0.004 P_{in} - 0.04) = 2.85 (0.004 * 100 - 0.04) = 1.026\text{ V}$$

Minimum absolute error = $|V_{out(nominal\ offset)} - V_{out(min)}|$

$$= |1.188 - 1.026| = 0.162$$

Figure 7: Question 5 Solution

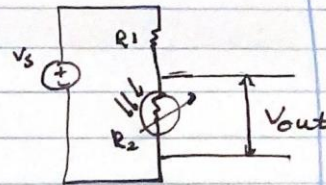
Question 6

Q6]

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(1) R2 in the bright light

given $\left[\begin{array}{l} R_2 \text{ in Bright light} = 200\Omega \\ V_s = V_{in} = 5\text{Volt} , R_1 = 10\text{k}\Omega \end{array} \right.$
 \Rightarrow using Voltage Divider Rule



$$V_{out} = V_{in} \cdot \frac{R_2}{R_2 + R_1} = \frac{5 \times 200\Omega}{200\Omega + 10000\Omega} = \frac{3500}{10200} = 0.327\text{V}$$

(2) R2 in the dark

$R_2 \text{ in dark} = 100\text{k}\Omega$

\Rightarrow using Voltage Divider Rule

$$V_{out} = V_{in} \cdot \frac{R_2}{R_2 + R_1} = \frac{5 \times 100\text{k}\Omega}{(100 + 10)\text{k}\Omega} = \frac{500}{110} = 4.54\text{V}$$

Figure 8: Question 6 Solution

Question 7

Q 7] $\tau = 38 \text{ sec}$, $f = 3 \text{ time/minute}$, $T = 20 \text{ sec}$
 $\tau = \frac{3}{60} = \frac{1}{20}$

$$\tau_d = \frac{\tan^{-1}(w\tau)}{w} = \frac{\tan^{-1}(2\pi f\tau)}{2\pi f}$$

$$= \frac{\tan^{-1}(2\pi * \frac{1}{20} * 38)}{2\pi * \frac{1}{20}}$$

$$= \frac{\tan^{-1}(2\pi * \frac{38}{20}) \text{ rad}}{2\pi (\frac{1}{20}) \text{ rad/s}}$$

$$= \frac{\tan^{-1}\left(\left(\frac{38}{20}\right)(2\pi) = \left(\frac{360}{2\pi}\right) \text{ degree}\right)}{\left(\frac{1}{20}\right)(2\pi) \left(\frac{360}{2\pi}\right) \text{ degree/s}}$$

$$= \frac{\tan^{-1}(684^\circ)}{18} \text{ seconds}$$

~~$\tau_d = 6.91 \text{ seconds}$~~

$\tau_d = 4.99534 \text{ seconds}$

Figure 9: Question 7 Solution

Question 8

The resistance changes in a strain gauge we can find it using this equation:

$$\Delta R = R_n \cdot GF \cdot \varepsilon$$

Where:

- ΔR : Resistance Change.
- R_n : Nominal resistance.
- GF : Gauge Factor.
- ε : Strain Applied.

From question given:

- $\varepsilon = 160 \mu m/m = 160 \times 10^{-6} m/m$
- $GF_{Metal} = 2.13$
- $GF_{Semiconductor} = -161$
- $R_n = 120 \Omega$

Now I will find the resistance change for metallic gauge:

$$\Delta R_{Metal} = R_n \times GF_{Metal} \times \varepsilon$$

$$= 120 \times 2.13 \times 160 \times 10^{-6} m/m$$

$$= 0.040896 \Omega$$

Then I will find the resistance change for semiconductor gauge:

$$\begin{aligned}\Delta R_{Semiconductor} &= R_n \times GF_{Semiconductor} \times \varepsilon \\ &= 120 \times -161 \times 160 \times 10^{-6} \text{ m/m} \\ &= -3.0912 \, \Omega\end{aligned}$$

Now, to find the absolute values of the resistance change we can use this equation:

$$\frac{|\Delta R_{Semiconductor}|}{|\Delta R_{Metal}|} = \frac{3.0912 \, \Omega}{0.040896 \, \Omega} = 75.61$$

From this result I can notice some points:

- Resistance change for metallic gauge is positive, this means the resistance increases approximately $0.040896 \, \Omega$ with strain.
- Resistance change for semiconductor gauge is negative, this means the resistance decrease approximately $3.0912 \, \Omega$ with strain.
- The semiconductor gauge much sensitive to strain than the metallic gauge for the given parameters.
- The resistance change in semiconductor gauge is 75.61 times larger than the resistance change in metallic gauge.

Question 9

From question given this value:

- Finger length (l_f) = $300 \mu m$
- Mass length (l_m) = $280 \mu m$
- Number of fingers (n) = 100
- Air gap (d_f) = $1 \mu m$
- Relative Permittivity (ϵ_r) = 7
- Measured capacitance change (ΔC) = $50.34 pF$

In this question is required to find the value of angle θ . I will use this equation to find the angle:

$$\begin{aligned}\theta &= \frac{n \cdot l_f \cdot \Delta C}{\epsilon_r \cdot l_m \cdot d_f} \\&= \frac{100 \times 300 \times 10^{-6} \times 50.34 \times 10^{-12}}{7 \times 280 \times 10^{-6} \times 1 \times 10^{-6}} \\&= 7.705 \times 10^{-4} \text{ degree}\end{aligned}$$

Question 10

From the question given:

- Input signal frequency (f) = 200 Hz
- Dynamic error = $\pm 5\%$
- Damping ratio (ζ) = 0.6

At first, I will convert the input frequency to angular frequency:

$$\omega = 2 \cdot \pi \cdot f$$

$$= 1256 \text{ rad/sec}$$

Calculation by hand shown in figure 10

Q 10]

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$f = 200 \text{ Hz}$, $\delta = 0.6$, Dynamic error $= \pm 5\%$

$$B(\omega) = \frac{A}{\sqrt{\left(1 - \left(\frac{\omega}{\omega_n}\right)^2\right)^2 + (2\delta \frac{\omega}{\omega_n})^2}}, \text{ let } R = \frac{\omega}{\omega_n}$$

$$B(\omega) = \frac{A}{\sqrt{(1 - R^2)^2 + (1.2R)^2}}, \text{ with dynamic error } = \pm 5\%$$

$$0.95A \leq \frac{A}{\sqrt{(1 - R^2)^2 + (1.2R)^2}} \leq 1.05A \Rightarrow \frac{1}{1.05} \leq \frac{1}{\sqrt{(1 - R^2)^2 + (1.2R)^2}} \leq \frac{1}{0.95}$$

$$\Rightarrow \left(\frac{1}{1.05}\right)^2 \leq 1 - 2R^2 + R^4 + 1.44R^2 \leq \left(\frac{1}{0.95}\right)^2$$

$$\left(\frac{1}{1.05}\right)^2 - 1 \leq R^4 - 0.56R^2 - 0.108033 \leq \left(\frac{1}{0.95}\right)^2 - 1$$

$$R^4 - 0.56R^2 - 0.108033 = 0 \Rightarrow \text{Solve this using cubic law, and let } R^2 = y$$

$$y^2 - 0.56y - 0.108033 = 0$$

$$y = 0.79589$$

$$y = R^2 \Rightarrow R = \sqrt{0.79589} = 0.8921$$

$$\frac{\omega}{\omega_n} \leq 0.8921 \Rightarrow \omega_n \geq \frac{2\pi(200)}{0.8921} \Rightarrow \omega_n \geq 1400 \text{ rad/sec}$$

Figure 10: Question 10 Solution


```
% Maha Maher Mali 1200746
zeta = input('Enter the value of damping ratio(zeta): ');
wn=input('Enter the value of wn in rad/sec : ');
numerator=[wn^2];
denominator=[1 2*zeta*wn wn^2];
Fun = tf(numerator,denominator)
ltiview(Fun)
```

Figure 11:MATLAB Code

```
>> Untitled
Enter the value of damping ratio (zeta): 0.6
Enter the value of wn in rad/sec: 1488

Fun =

          2.214e06
-----
s^2 + 1786 s + 2.214e06
```

Figure 12:MATLAB Result

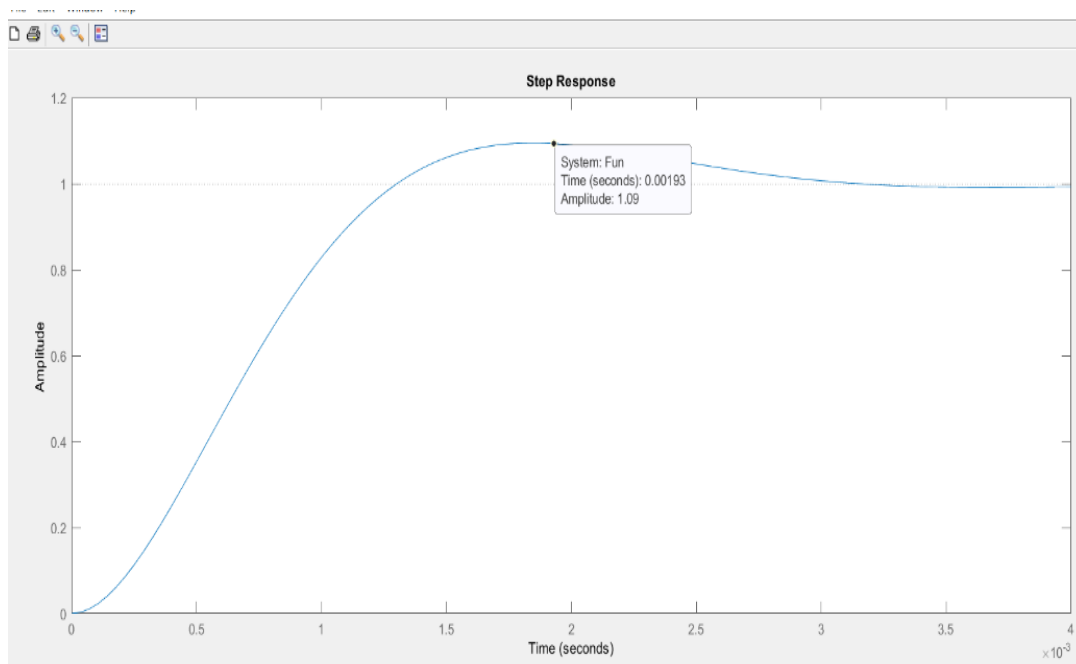


Figure 13: Step Response

Question 11

❖ What is Load cell?

A load cell is a transducer that is used to create an electrical signal whose magnitude is directly proportional to the force being measured. It is basically a device that measures strain and then converts force into electric energy which serves as a measurement for scientists and workers.[1]

❖ HX711 Load Cell Amplifier

The Load Cell Amplifier is a small breakout board for the HX711 IC that allows you to easily read load cells to measure weight. By connecting the amplifier to your microcontroller, you will be able to read the changes in the resistance of the load cell, and with some calibration, you'll be able to get very accurate weight measurements.[1]

❖ Circuit Diagram

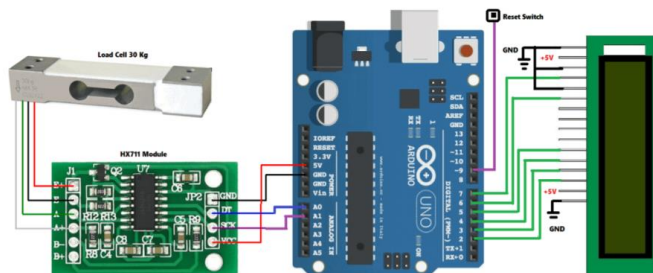


Figure 14: Scale using strain gauge load cell [1]

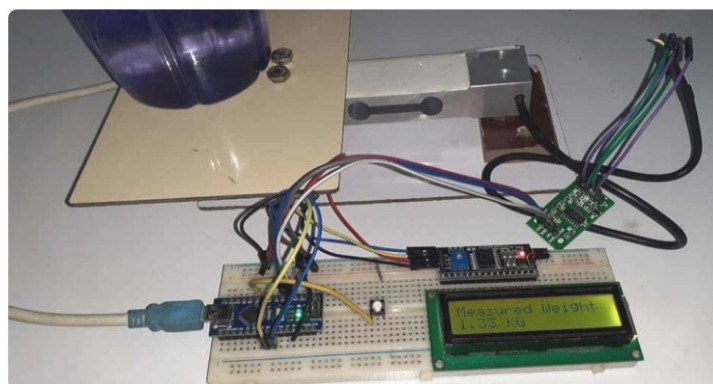


Figure 15: Scale [2]

❖ Connection on the Proteus

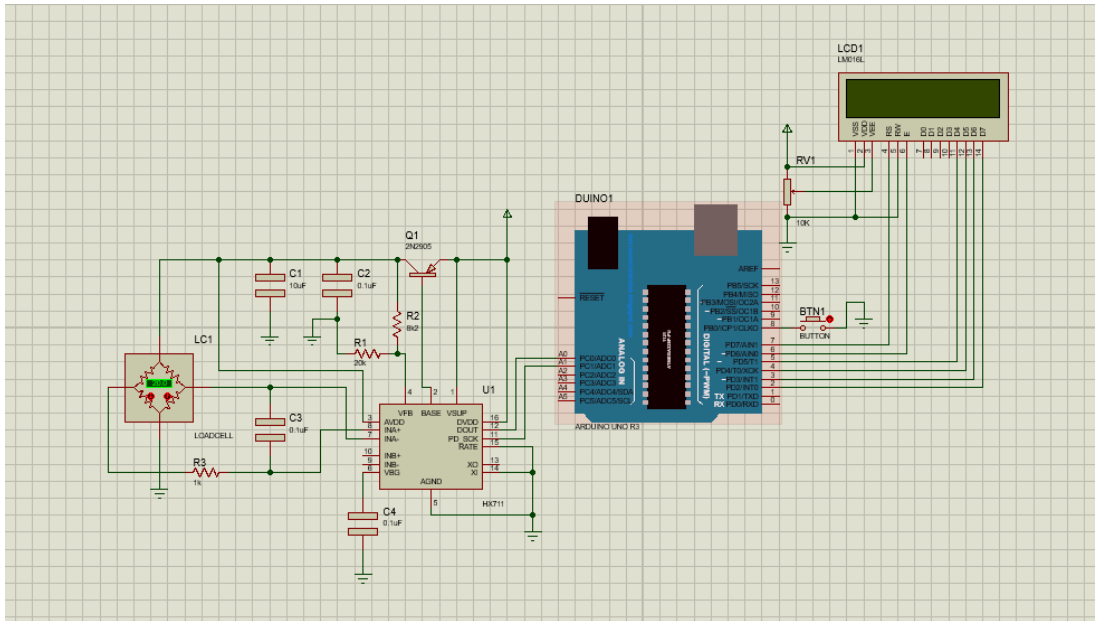


Figure 16: Connection on the Proteus [3]

❖ Components Required for this Weighing Scale Project

S.N.	Components Name	Quantity
1	Arduino Nano	1
2	16x2 LCD Display	1
3	Load Cell	1
4	HX711	1
5	Push Button	1
6	Connecting Wires	10
7	Breadboard	1

Figure 17: Components

❖ Code

```
#include <LiquidCrystal.h>
LiquidCrystal lcd(7, 6, 5, 4, 3, 2);

#define DT A0
#define SCK A1
#define sw 9

long sample=0;
float val=0;
long count=0;

unsigned long readCount(void)
{
    unsigned long Count;
    unsigned char i;
    pinMode(DT, OUTPUT);
    digitalWrite(DT,HIGH);
    digitalWrite(SCK,LOW);
    Count=0;
    pinMode(DT, INPUT);
    while(digitalRead(DT));
    for (i=0;i<24;i++)
    {
        digitalWrite(SCK,HIGH);
        Count=Count<<1;
        digitalWrite(SCK,LOW);
        if(digitalRead(DT))
            Count++;
    }
    digitalWrite(SCK,HIGH);
    Count=Count^0x800000;
    digitalWrite(SCK,LOW);
    return(Count);
}

void setup()
{
    pinMode(SCK, OUTPUT);
    pinMode(sw, INPUT_PULLUP);
    lcd.begin(16, 2);
    lcd.print(" Weight ");
    lcd.setCursor(0,1);
    lcd.print(" Measurement ");
}
```

```

delay(1000);
lcd.clear();
calibrate();
}

void loop()
{
count= readCount();
int w=(((count-sample)/val)-2*((count-sample)/val));
lcd.setCursor(0,0);
lcd.print("Measured Weight");
lcd.setCursor(0,1);
lcd.print(w);
lcd.print("g ");

if(digitalRead(sw)==0)
{
val=0;
sample=0;
w=0;
count=0;
calibrate();
}
}

void calibrate()
{
lcd.clear();
lcd.print("Calibrating...");
lcd.setCursor(0,1);
lcd.print("Please Wait...");
for(int i=0;i<100;i++)
{
count=readCount();
sample+=count;
}
sample/=100;
lcd.clear();
lcd.print("Put 100g & wait");
count=0;
while(count<1000)
{
count=readCount();
count=sample-count;
}
}

```

```
lcd.clear();  
lcd.print("Please Wait....");  
delay(2000);  
for(int i=0;i<100;i++)  
{  
  count=readCount();  
  val+=sample-count;  
}  
val=val/100.0;  
val=val/100.0; // put here your calibrating weight  
lcd.clear();  
}
```

References

[1] <https://how2electronics.com/weighing-machine-arduino-load-cell-hx711/> .

Accessed on 7-12-2023 at 11:50 AM.

[2] <https://how2electronics.com/weighing-scale-40kg-load-cell-hx711-arduino/> .

Accessed on 7-12-2023 at 12:50 PM.

[3] https://www.youtube.com/watch?v=gpofOo4_PtA .

Accessed on 7-12-2023 at 12:50 PM.